

GI3302

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

BVDSS	25V
RDS(ON)	50mΩ
ID	16A

Description

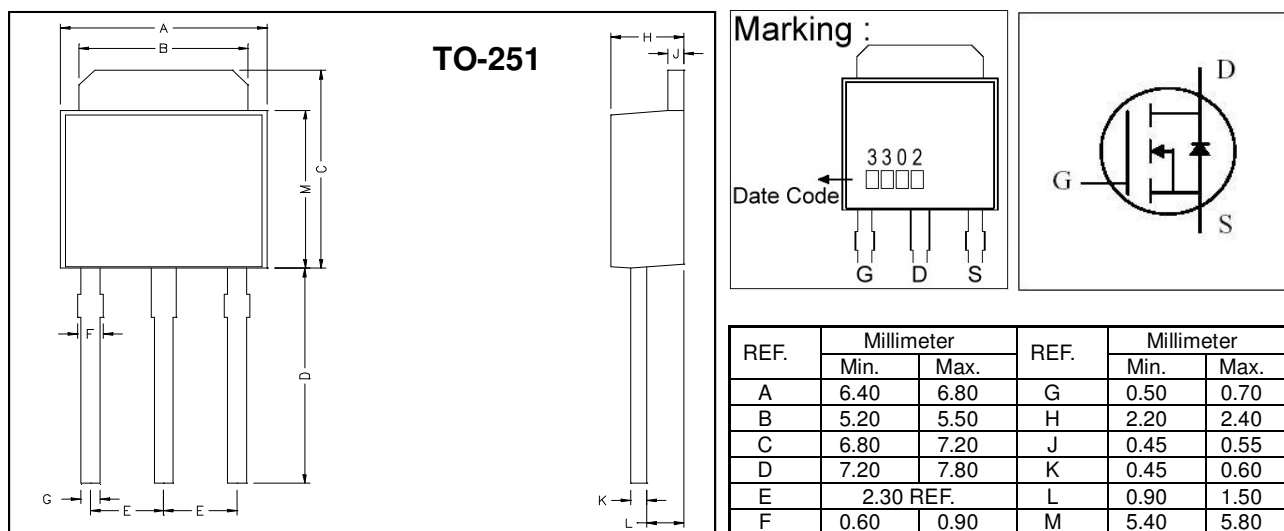
The GI3302 provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The through-hole version (TO-251) is available for low-profile applications and suited for low voltage applications such as DC/DC converters.

Features

- *Low Gate Charge
- *Simple Drive Requirement
- *Fast Switching

Package Dimensions



Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=25^\circ C$	16	A
Continuous Drain Current, $V_{GS}@10V$	$I_D @T_C=100^\circ C$	10	A
Pulsed Drain Current ¹	I_{DM}	25	A
Total Power Dissipation	$P_D @T_C=25^\circ C$	20	W
Linear Derating Factor		0.16	W/ $^\circ C$
Operating Junction and Storage Temperature Range	T_j, T_{stg}	-55 ~ +150	$^\circ C$

Thermal Data

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-case Max.	Rthj-c	6.4	$^\circ C/W$
Thermal Resistance Junction-ambient Max.	Rthj-a	110	$^\circ C/W$

Electrical Characteristics(T_j = 25°C Unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source Breakdown Voltage	BV _{DSS}	25	-	-	V	V _{GS} =0, I _D =250uA
Gate Threshold Voltage	V _{GS(th)}	2.0	-	4.0	V	V _{DS} =V _{GS} , I _D =250uA
Gate-Source Leakage Current	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V
Drain-Source Leakage Current(T _j =25°C)	I _{DSS}	-	-	1	uA	V _{DS} =25V, V _{GS} =0
Drain-Source Leakage Current(T _j =150°C)		-	-	25	uA	V _{DS} =20V, V _{GS} =0
Static Drain-Source On-Resistance ²	R _{D(ON)}	-	-	50	mΩ	V _{GS} =10V, I _D =8A
Total Gate Charge ²	Q _g	-	7.4	13	nC	I _D =10A V _{DS} =20V V _{GS} =10V
Gate-Source Charge	Q _{gs}	-	2.2	-		
Gate-Drain ("Miller") Change	Q _{gd}	-	4.2	-		
Turn-on Delay Time ²	T _{d(on)}	-	8	-	ns	V _{DS} =15V I _D =16A V _{GS} =10V R _G =3.3Ω R _D =0.94Ω
Rise Time	T _r	-	7.4	-		
Turn-off Delay Time	T _{d(off)}	-	11	-		
Fall Time	T _f	-	3	-		
Input Capacitance	C _{iss}	-	164	290	pF	V _{GS} =0V V _{DS} =25V f=1.0MHz
Output Capacitance	C _{oss}	-	158	-		
Reverse Transfer Capacitance	C _{rss}	-	62	-		

Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward On Voltage ²	V _{SD}	-	-	1.3	V	I _S =16A, V _{GS} =0V
Reverse Recovery Time	T _{rr}	-	29	-	ns	I _S =16A, V _{GS} =0V di/dt=100A/μs
Reverse Recovery Charge	Q _{rr}	-	21	-	nC	

Notes: 1. Pulse width limited by safe operating area.

2. Pulse width ≤ 300us, duty cycle ≤ 2%.

Characteristics Curve

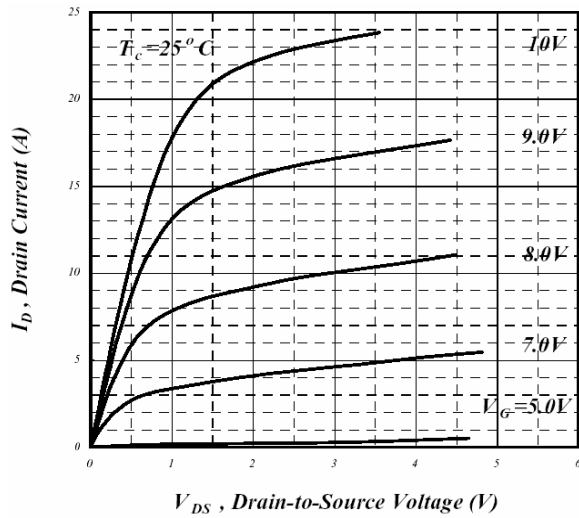


Fig 1. Typical Output Characteristics

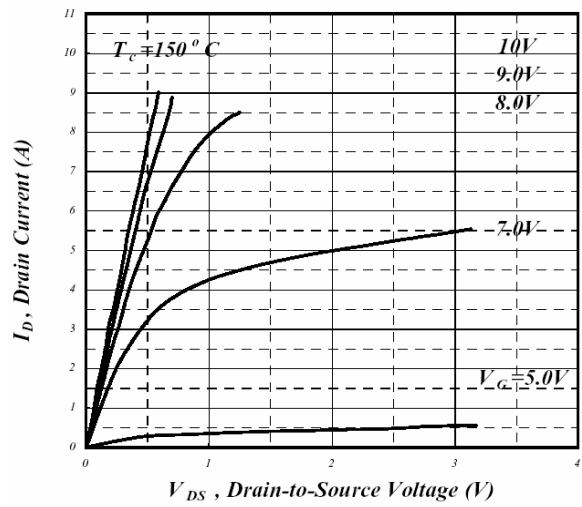


Fig 2. Typical Output Characteristics

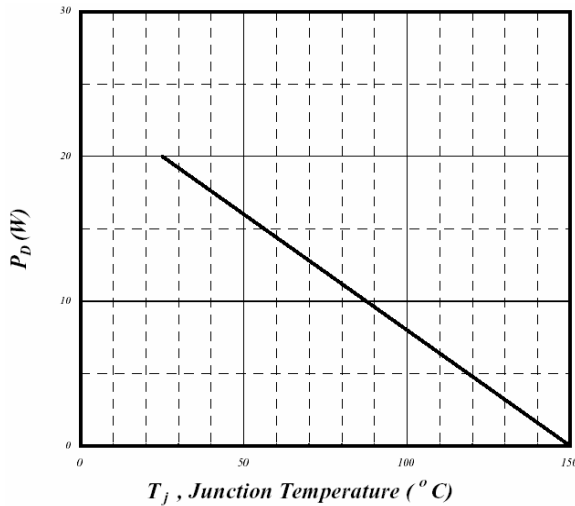


Fig 3. Type Power Dissipation

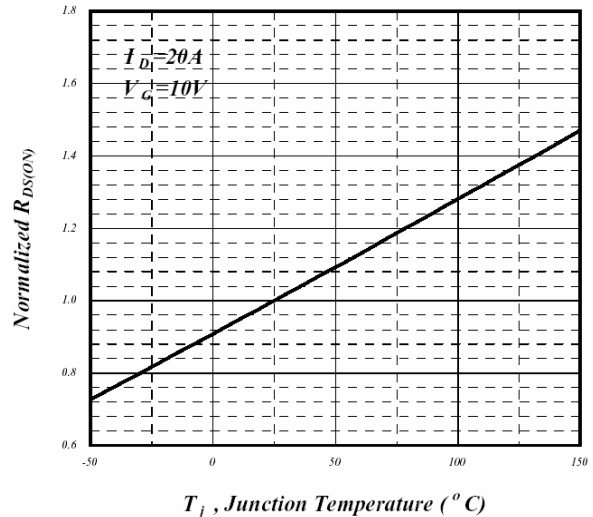


Fig 4. Normalized On-Resistance v.s. Junction Temperature

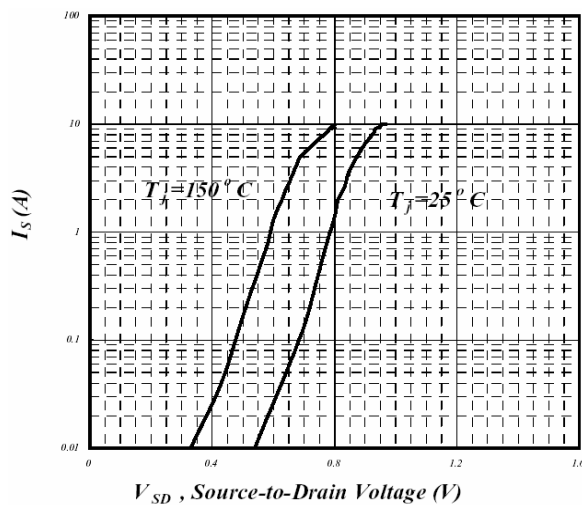


Fig 5. Forward Characteristics of Reverse Diode

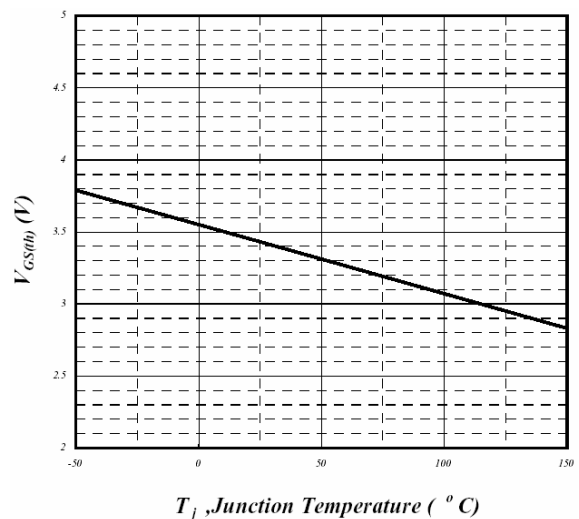


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

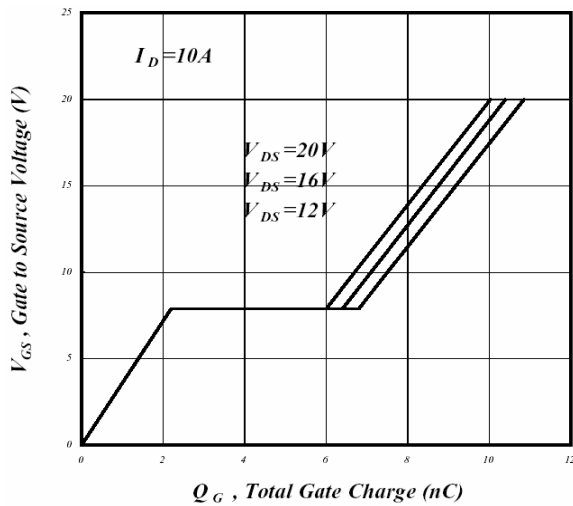


Fig 7. Gate Charge Characteristics

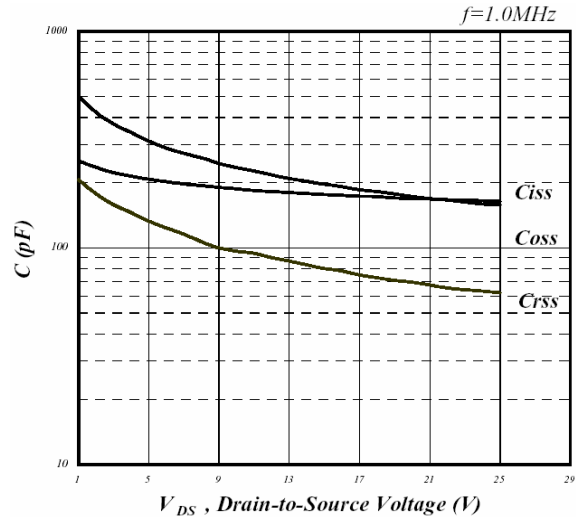


Fig 8. Typical Capacitance Characteristics

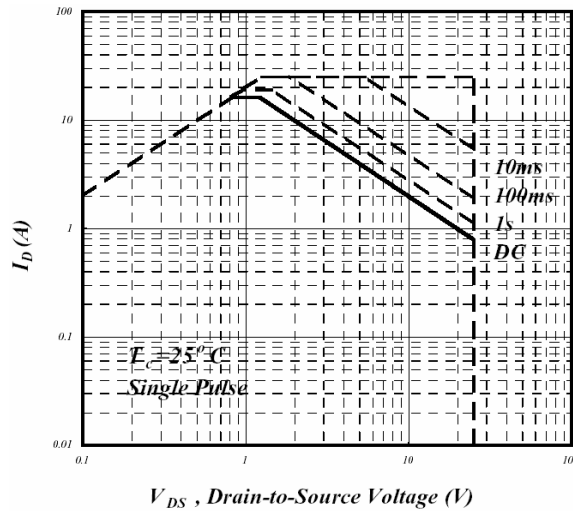


Fig 9. Maximum Safe Operating Area

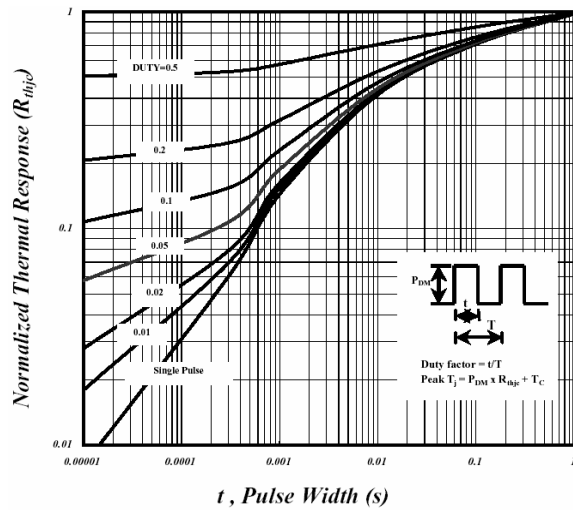


Fig 10. Effective Transient Thermal Impedance



Fig 11. Switching Time Waveform

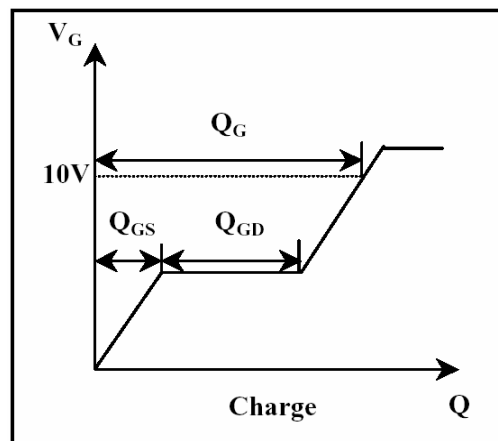


Fig 12. Gate Charge Waveform

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